

FORMATION OF SILICON OXIDE COATING FILM

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Abstract

PURPOSE: A substrate is coated with an organosilicon compound containing ultra- violet absorbing substances and sintered in an oxidative atmosphere as ultraviolet rays are irradiated to effect oxidation whereby good coating films of silicon oxide are formed at relatively low temperatures.

CONSTITUTION: A substrate is coated with an organosilicon compound containing an ultraviolet absorbing substance such as an organotitanium compound and placed in a heating furnace, then baked in an oxidative atmosphere at about 350 deg.C, as ultraviolet rays are irradiated to oxidize the organosilicon compound and form coating films of silicon oxide on the substrate. Thus, silicon oxide coating films used as optical interference films with high refractive index.